

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (currently amended) A linear device, comprising:  
~~including~~

a gate electrode, a gate insulating region, a source region, a drain region, and a semiconductor region, ~~characterized in that~~

wherein said semiconductor region is arranged between said source region comprising one or a plurality of source region(s) and said drain region comprising one or a plurality of drain region(s), in a radial direction within a cross section of a device region, so that a part of said gate insulating region is contacted with said semiconductor region, and

wherein said semiconductor region is made of a semiconductor material having a different conductivity type than those of said source and drain regions.

2. (original) The linear device of claim 1, wherein said gate electrode and said gate insulating region are arranged inside or outside said source region(s) and said drain region(s).

3. (previously presented) The linear device of claim 1, wherein said linear device comprises, at a center, one of: a hollow region; an electric conductor region; said gate electrode;

said source region; said drain region; another insulating region different from said gate insulating region; and another semiconductor region different from said semiconductor region.

4. (previously presented) The linear device of claim 1, wherein said linear device comprises a plurality of device regions through separation regions therebetween, respectively, in a longitudinal direction of a linear body constituting said linear device.

5. (previously presented) The linear device of claim 1, wherein said gate electrode, gate insulating region, source region(s), drain region(s), and/or semiconductor region constituting said linear device are formed of an organic semiconductor or electroconductive polymer.

6. (previously presented) The linear device of claim 2, wherein said linear device comprises, at a center, one of: a hollow region; an electric conductor region; said gate electrode; said source region; said drain region; another insulating region different from said gate insulating region; and another semiconductor region different from said semiconductor region.

7. (previously presented) The linear device of claim 2, wherein said linear device comprises a plurality of device regions through separation regions therebetween, respectively, in a longitudinal direction of a linear body constituting said linear device.

8. (previously presented) The linear device of claim 3, wherein said linear device comprises a plurality of device regions through separation regions therebetween, respectively, in a longitudinal direction of a linear body constituting said linear device.

9. (previously presented) The linear device of claim 2, wherein said gate electrode, gate insulating region, source region(s), drain region(s), and/or semiconductor region constituting said linear device are formed of an organic semiconductor or electroconductive polymer.

10. (previously presented) The linear device of claim 3, wherein said gate electrode, gate insulating region, source region(s), drain region(s), and/or semiconductor region constituting said linear device are formed of an organic semiconductor or electroconductive polymer.

11. (previously presented) The linear device of claim 4, wherein said gate electrode, gate insulating region, source region(s), drain region(s), and/or semiconductor region constituting said linear device are formed of an organic semiconductor or electroconductive polymer.

12. (new) A linear device comprising:

a longitudinally extended gate electrode surrounded by an annular gate insulator;

a longitudinally extended annular semiconductor region surrounding said gate insulator;

plural longitudinally extended first conductive regions between said gate insulator and said semiconductor region, said plural first conductive regions being separated from each other so that a portion of said semiconductor region directly contacts said gate insulator between adjacent ones of said plural first conductive regions;

a longitudinally extended second conductive region around said semiconductor region and separated from said plural first conductive regions by said semiconductor region; and

an annular protection region surrounding said second conductive region.

13. (new) The linear device of claim 12, wherein said first conductive regions are source regions and said second conductive region is a drain region.

14. (new) The linear device of claim 12, wherein said first conductive regions are drain regions and said second conductive region is a source region.

15. (new) A linear device comprising:

a longitudinally extended first conductive region surrounded by an annular semiconductor region;

a longitudinally extended annular gate insulator surrounding said semiconductor region;

plural longitudinally extended second conductive regions between said gate insulator and said semiconductor region, said plural second conductive regions being separated

from each other so that a portion of said semiconductor region directly contacts said gate insulator between adjacent ones of said second conductive regions;

a longitudinally extended gate electrode surrounding said gate insulator and separated from said second conductive regions by said gate insulator; and

an annular protection region surrounding said gate electrode.

16. (new) The linear device of claim 12, wherein said first conductive region is a source region and said second conductive regions are drain regions.

17. (new) The linear device of claim 12, wherein said first conductive region is a drain region and said second conductive regions are source regions.